

## NCE N-Channel Super Trench II Power MOSFET

### Description

The NCEP11N10AQU uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(on)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### Application

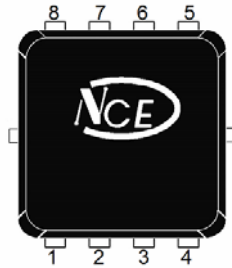
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

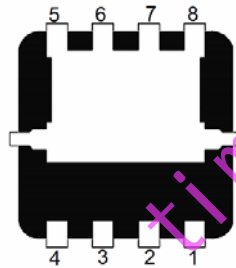
- $V_{DS} = 100V, I_D = 55A$
- $R_{DS(on)} = 10.5m\Omega$  (typical) @  $V_{GS} = 10V$
- $R_{DS(on)} = 13.5m\Omega$  (typical) @  $V_{GS} = 4.5V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

**100% UIS TESTED!**  
**100% ΔVds TESTED!**

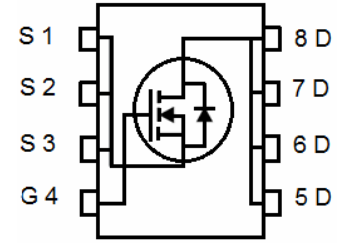
### DFN 3.3X3.3



Top View



Bottom View



Schematic Diagram

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP11N10AQU	NCEP11N10AQU	DFN3.3X3.3-8L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	55	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	39	A
Pulsed Drain Current	$I_{DM}$	220	A
Maximum Power Dissipation	$P_D$	70	W
Derating factor		0.56	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	156	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	1.79	$^\circ C/W$
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## Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.1	1.8	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=25A$	-	10.5	11.8	m $\Omega$
		$V_{GS}=4.5V, I_D=25A$	-	13.5	16	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=25A$	25	-	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V$ $F=1.0\text{MHz}$	-	2050	-	PF
Output Capacitance	$C_{oss}$		-	180	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	21	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=25A$ $V_{GS}=10V, R_G=3\Omega$	-	16	-	nS
Turn-on Rise Time	$t_r$		-	18	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	32	-	nS
Turn-Off Fall Time	$t_f$		-	10	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=50V, I_D=25A$ $V_{GS}=10V$	-	42	-	nC
Gate-Source Charge	$Q_{gs}$		-	7.8	-	nC
Gate-Drain Charge	$Q_{gd}$		-	11	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=25A$	-		1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	55	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ\text{C}, I_F = 25A$ $di/dt = 100A/\mu s$ (Note 3)	-	45	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	95	-	nC

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^\circ\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

Typical Electrical and Thermal Characteristics

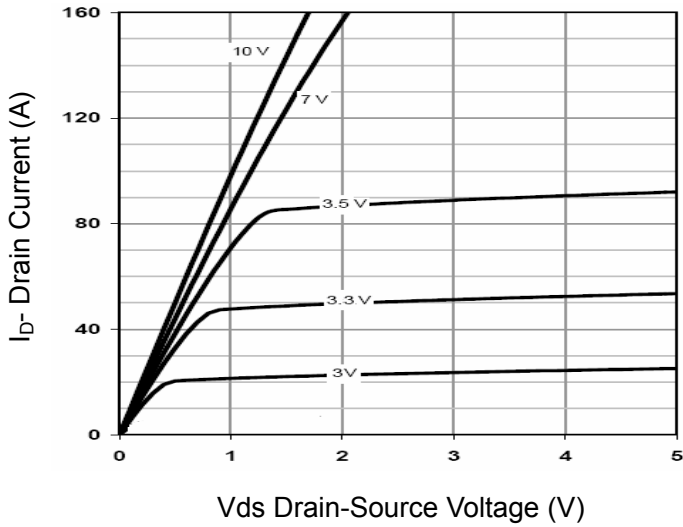


Figure 1 Output Characteristics

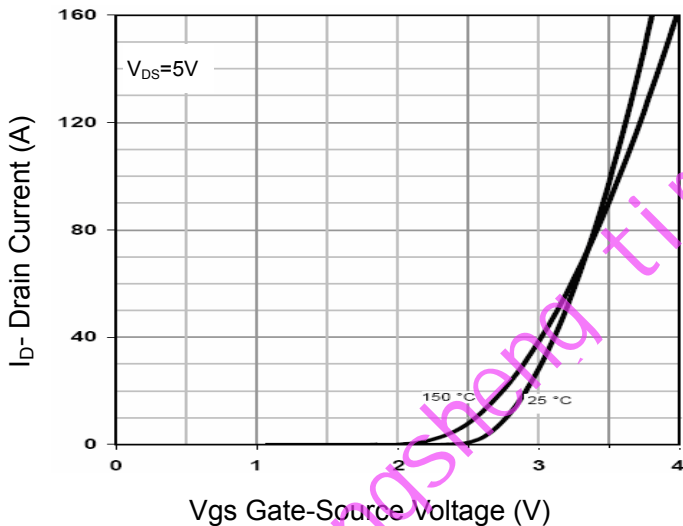


Figure 2 Transfer Characteristics

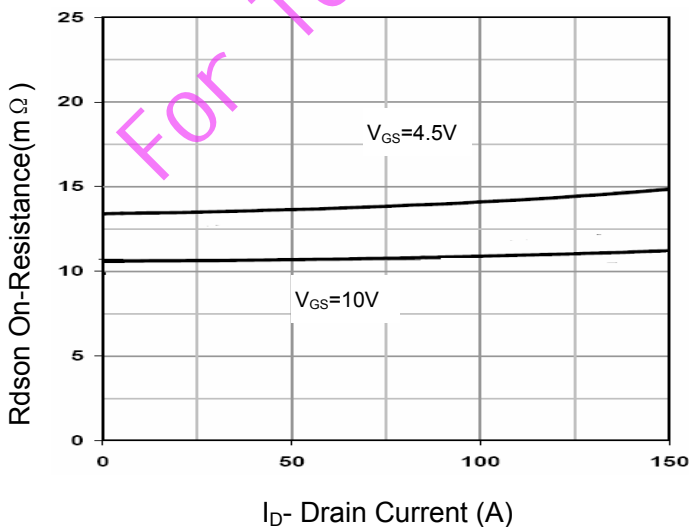


Figure 3 Rdson- Drain Current

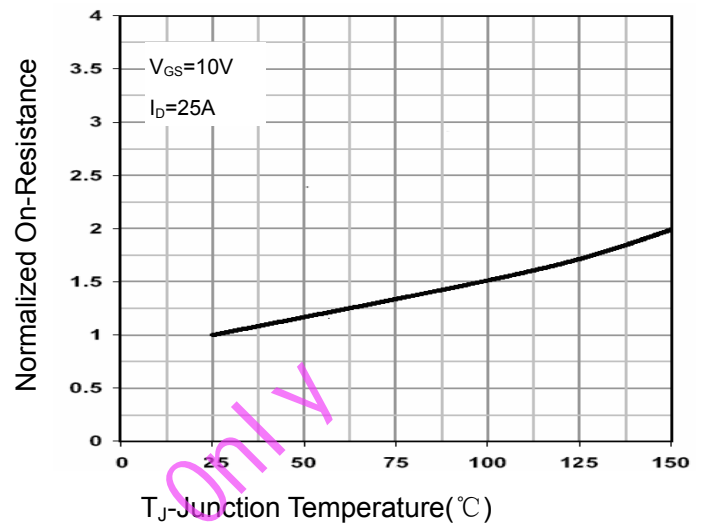


Figure 4 Rdson-Junction Temperature

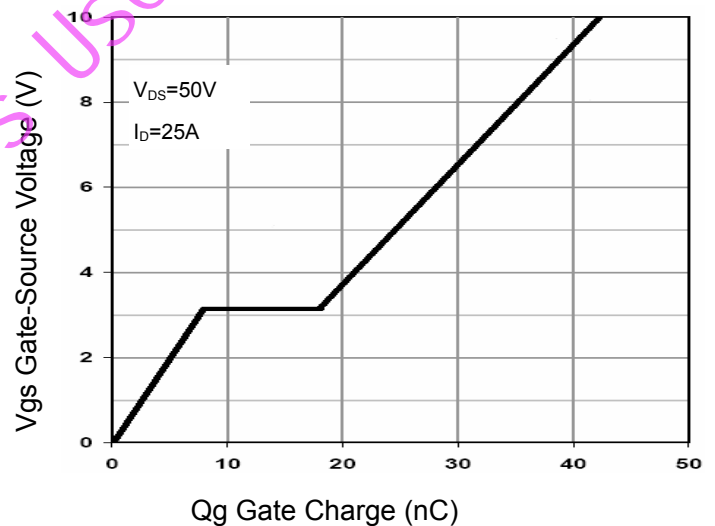


Figure 5 Gate Charge

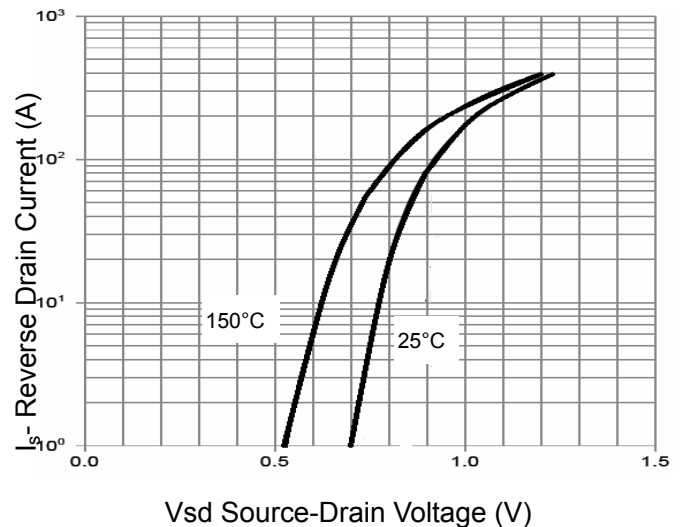
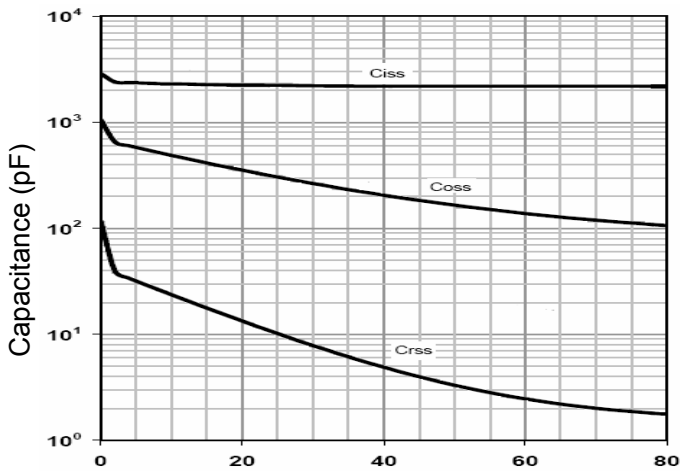
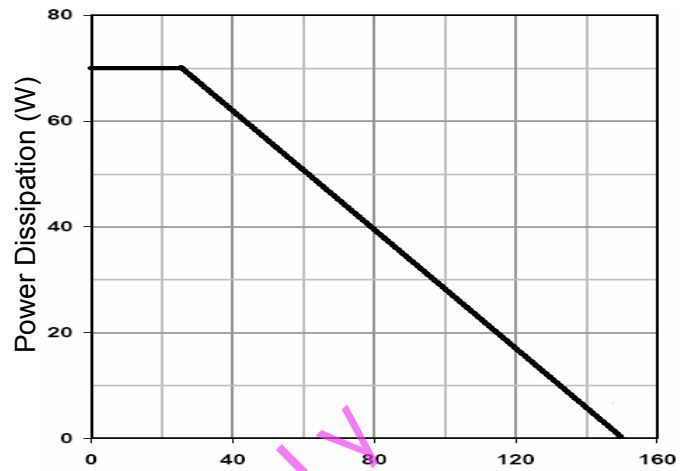


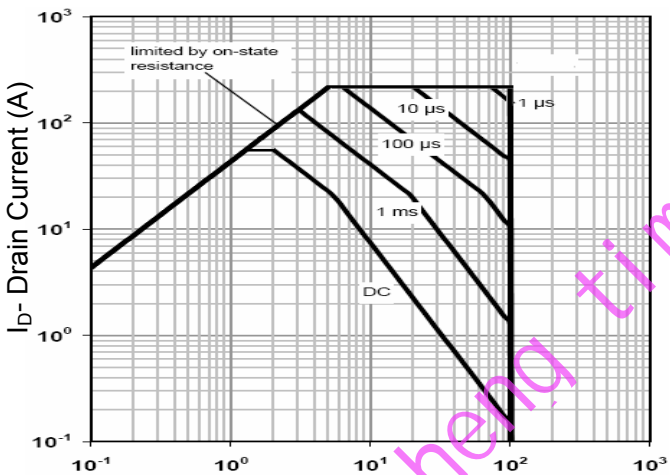
Figure 6 Source- Drain Diode Forward



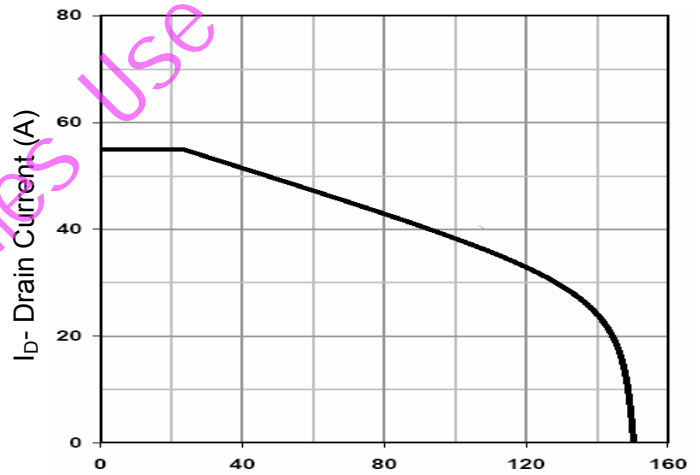
V<sub>ds</sub> Drain-Source Voltage (V)  
**Figure 7 Capacitance vs V<sub>ds</sub>**



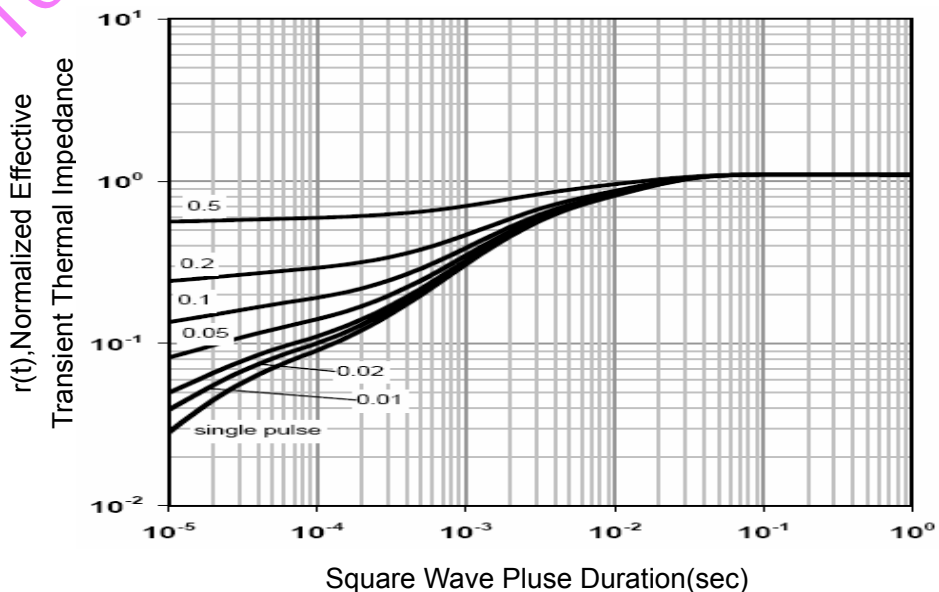
T<sub>c</sub> Case Temperature(°C)  
**Figure 9 Power De-rating**



V<sub>ds</sub> Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area**

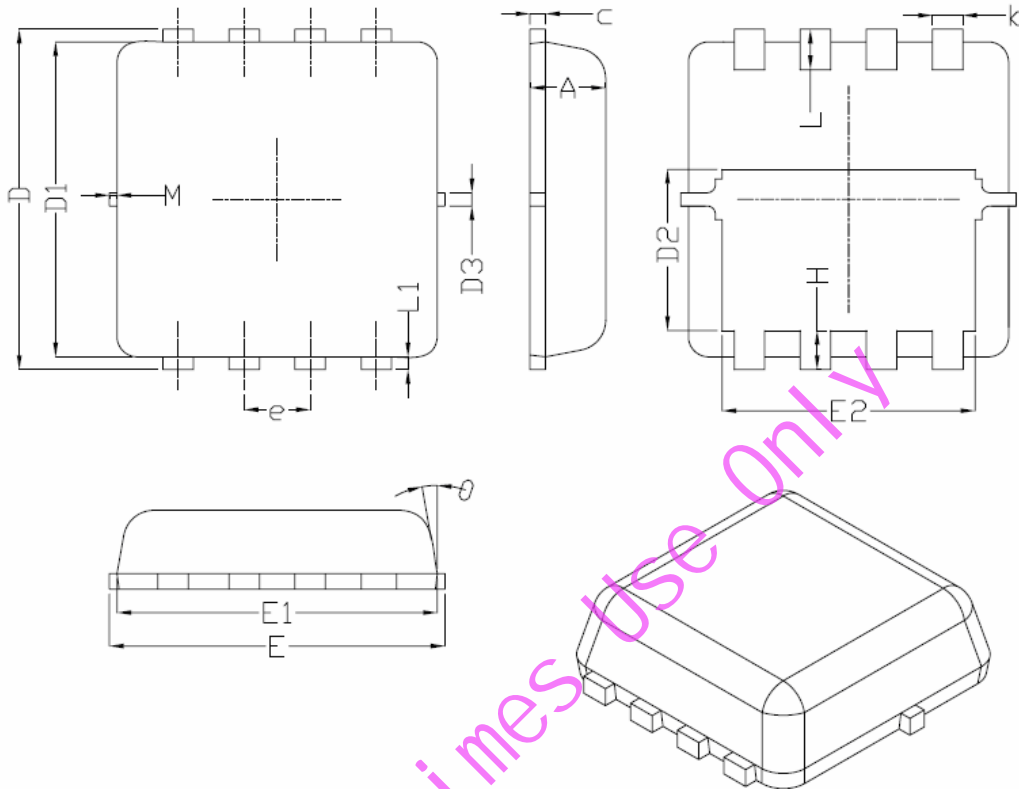


T<sub>c</sub> Case Temperature (°C)  
**Figure 10 Current De-rating**



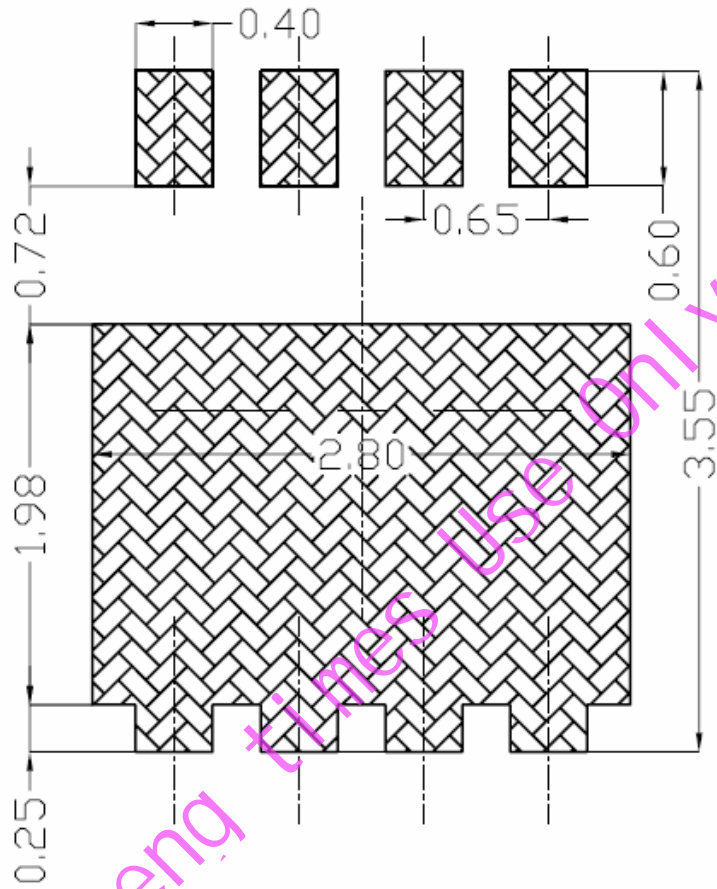
Square Wave Pulse Duration(sec)  
**Figure 11 Normalized Maximum Transient Thermal Impedance**

## DFN3.3X3.3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

## Land Pattern (Only for Reference)



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